

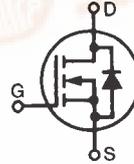


**PolarHT™  
Power MOSFET**

**IXTA 62N15P  
IXTP 62N15P  
IXTQ 62N15P**

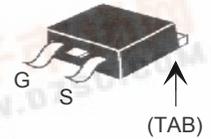
**V<sub>DSS</sub> = 150 V  
I<sub>D25</sub> = 62 A  
R<sub>DS(on)</sub> ≤ 40 mΩ**

N-Channel Enhancement Mode  
Avalanche Rated

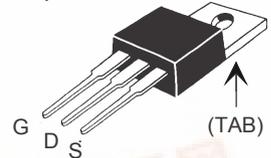


Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25° C to 175° C	150	V
V <sub>DGR</sub>	T <sub>J</sub> = 25° C to 175° C; R <sub>GS</sub> = 1 MΩ	150	V
V <sub>GS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25° C	62	A
I <sub>DM</sub>	T <sub>C</sub> = 25° C, pulse width limited by T <sub>JM</sub>	150	A
I <sub>AR</sub>	T <sub>C</sub> = 25° C	50	A
E <sub>AR</sub>	T <sub>C</sub> = 25° C	30	mJ
E <sub>AS</sub>	T <sub>C</sub> = 25° C	1.0	J
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , di/dt ≤ 100 A/μs, V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150° C, R <sub>G</sub> = 10 Ω	10	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25° C	350	W
T <sub>J</sub>		-55 ... +175	°C
T <sub>JM</sub>		175	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6 mm (0.062 in.) from case for 10 s	300	°C
T <sub>SOLD</sub>	Plastic body for 10 s	2600	°C
Md	Mounting torque (TO-3P / TO-220)	1.13/10	Nm/lb.in.
Weight	TO-3P	5.5	g
	TO-220	4	g
	TO-263	3	g

TO-263 (IXTA)



TO-220 (IXTP)



TO-3P (IXTQ)



G = Gate      D = Drain  
S = Source      TAB = Drain

Symbol	Test Conditions (T <sub>J</sub> = 25° C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	150		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3.0		5.5 V
I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V <sub>DC</sub> , V <sub>DS</sub> = 0			±100 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> V <sub>GS</sub> = 0 V T <sub>J</sub> = 150° C			25 μA
				250 μA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 I <sub>D25</sub> Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %	33	40	mΩ

**Features**

- 1 International standard packages
- 1 Unclamped Inductive Switching (UIS) rated
- 1 Low package inductance - easy to drive and to protect

**Advantages**

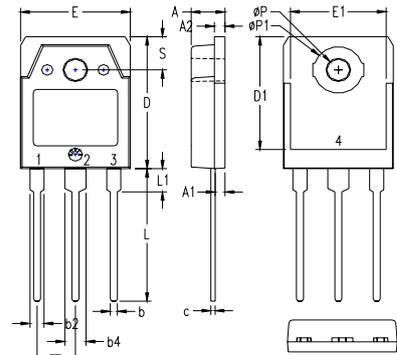
- 1 Easy to mount
- 1 Space savings
- 1 High power density



Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{ V}$ ; $I_D = 0.5 I_{D25}$ , pulse test	14	24	S
$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$		2250	pF
$C_{oss}$			660	pF
$C_{rss}$			185	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = 0.5 I_{D25}$ $R_G = 10\ \Omega$ (External)		27	ns
$t_r$			38	ns
$t_{d(off)}$			76	ns
$t_f$			35	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = 0.5 I_{D25}$		70	nC
$Q_{gs}$			20	nC
$Q_{gd}$			38	nC
$R_{thJC}$				$0.42^\circ\text{C/W}$
$R_{thCS}$	(TO-3P)	0.21		$^\circ\text{C/W}$
	(TO-220)	0.25		$^\circ\text{C/W}$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{ V}$			62 A
$I_{SM}$	Repetitive			150 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 25\text{ A}$ , $-di/dt = 100\text{ A}/\mu\text{s}$		150	ns
$Q_{RM}$	$V_R = 100\text{ V}$ , $V_{GS} = 0\text{ V}$		2.0	$\mu\text{C}$

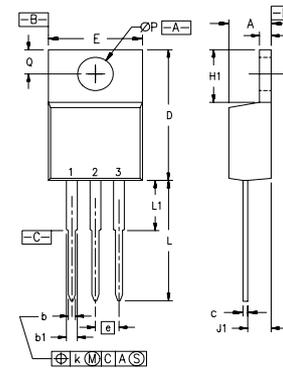
### TO-3P (IXTQ) Outline



- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
ØP1	.126	.134	3.20	3.40
S	.272	.280	6.90	7.10
	.193	.201	4.90	5.10

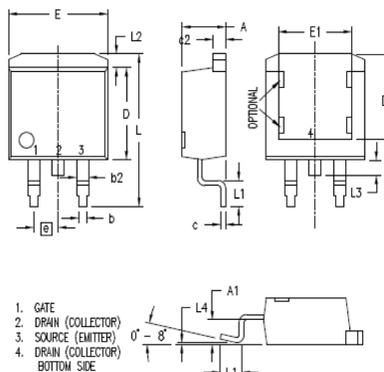
### TO-220 (IXTP) Outline



- Pins: 1 - Gate      2 - Drain
- 3 - Source    Tab - Drain

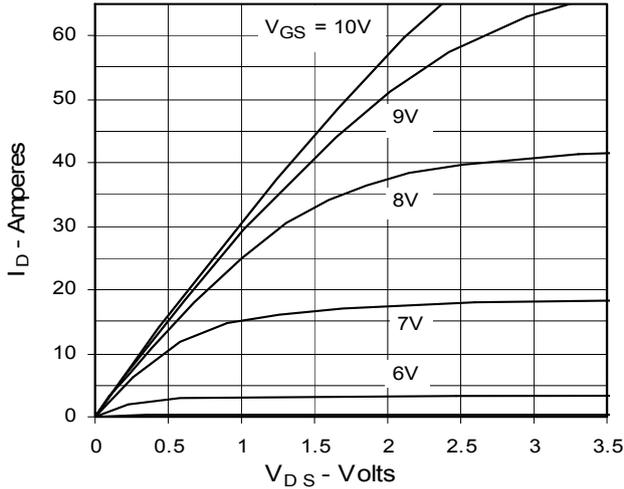
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

### TO-263 (IXTA) Outline

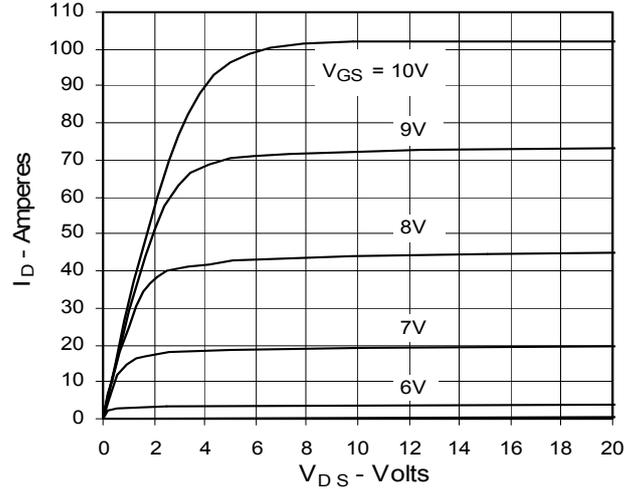


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

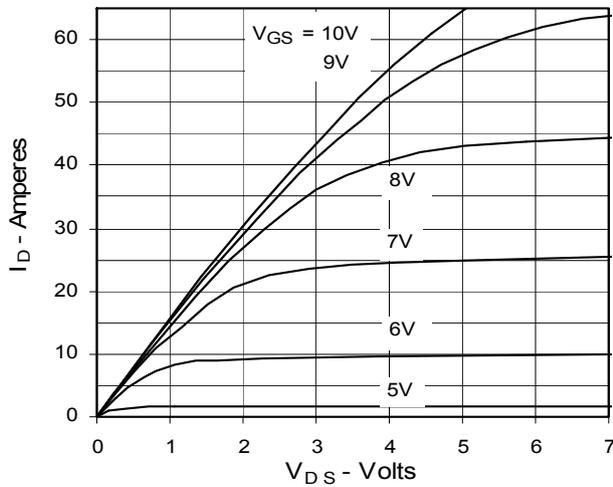
**Fig. 1. Output Characteristics  
@ 25°C**



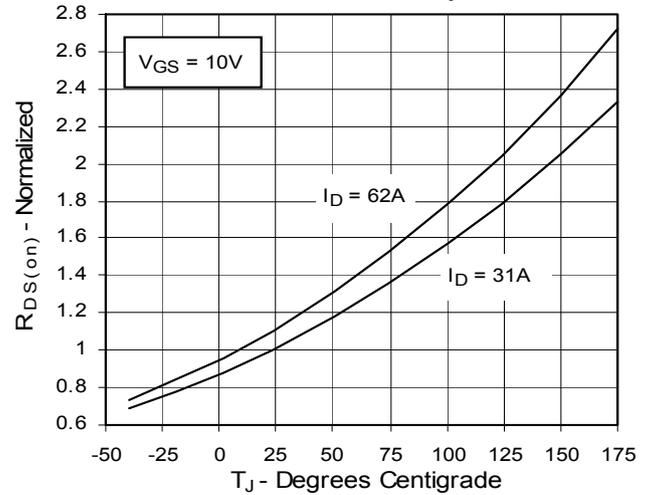
**Fig. 2. Extended Output Characteristics  
@ 25°C**



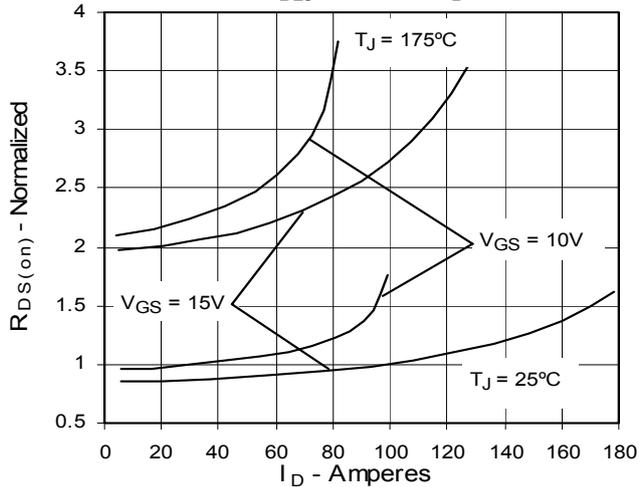
**Fig. 3. Output Characteristics  
@ 150°C**



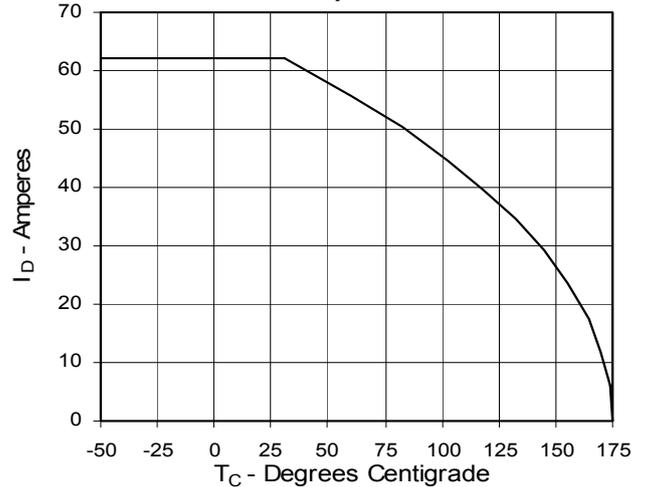
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$   
Value vs. Junction Temperature**



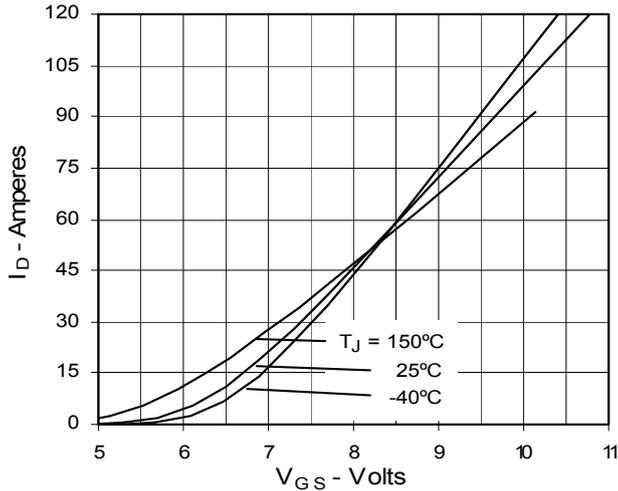
**Fig. 5.  $R_{DS(on)}$  Normalized to  
0.5  $I_{D25}$  Value vs.  $I_D$**



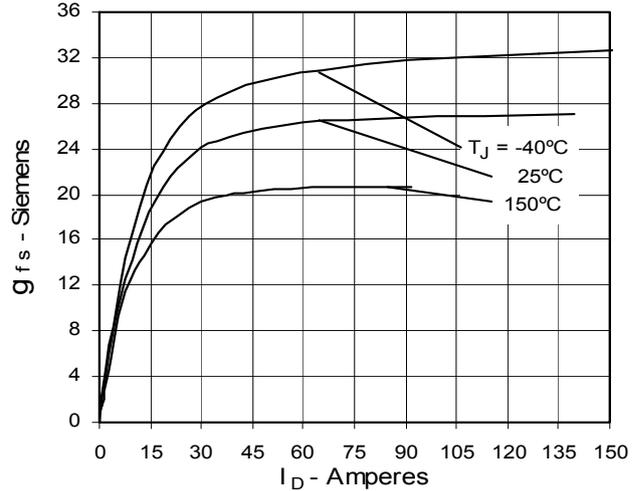
**Fig. 6. Drain Current vs. Case  
Temperature**



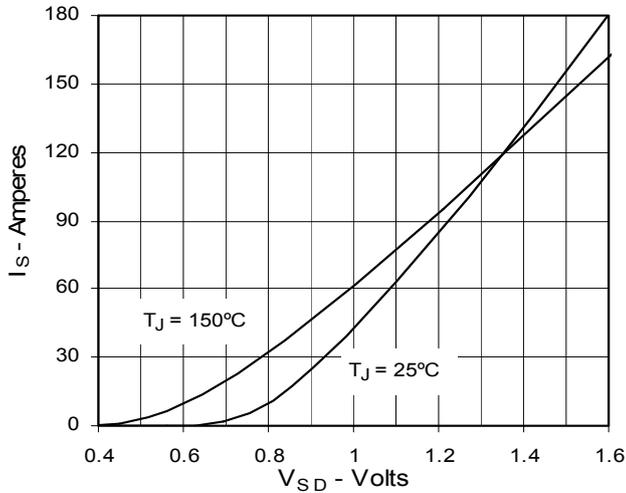
**Fig. 7. Input Admittance**



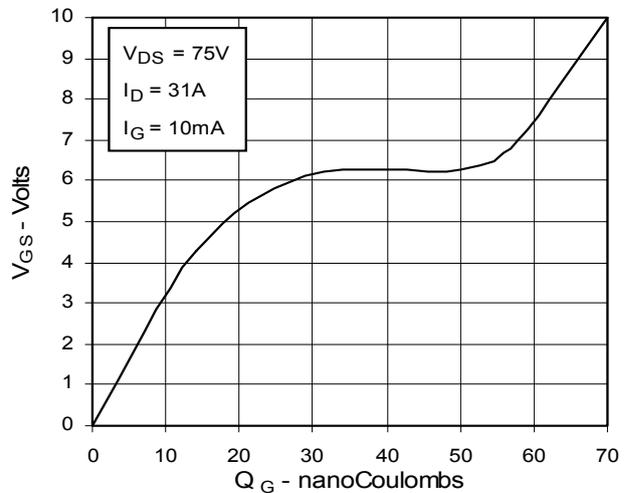
**Fig. 8. Transconductance**



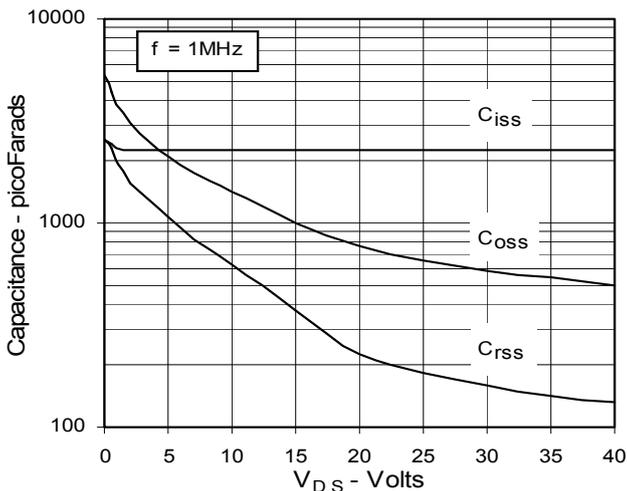
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

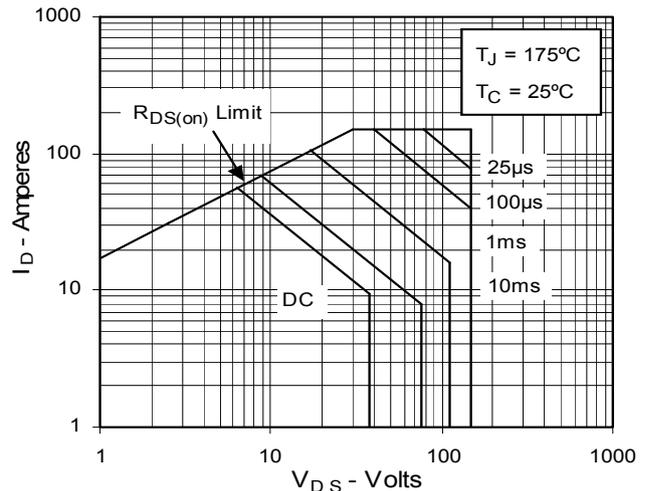


Fig. 13. Maximum Transient Thermal Resistance

